

ZXMP6A17E6

60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max $T_A = 25^\circ C$ (Note 5)
-60V	125m Ω @ $V_{GS} = -10V$	-3.0 A
	190m Ω @ $V_{GS} = -4.5V$	-2.4 A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

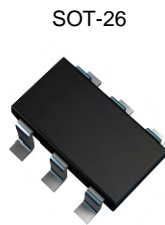
- DC-DC Converters
- Power management functions
- Disconnect switches
- Motor control

Features and Benefits

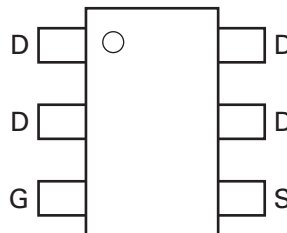
- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low input capacitance
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

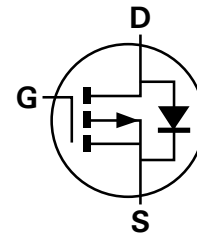
- Case: SOT-26
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.018 grams (approximate)



Top View



Pin Out - Top View



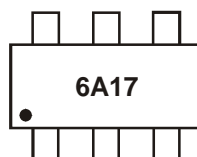
Equivalent Circuit

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A17E6TA	6A17	7	8	3,000

- Notes:
1. No purposefully added lead
 2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



6A17 = Product Type Marking Code

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

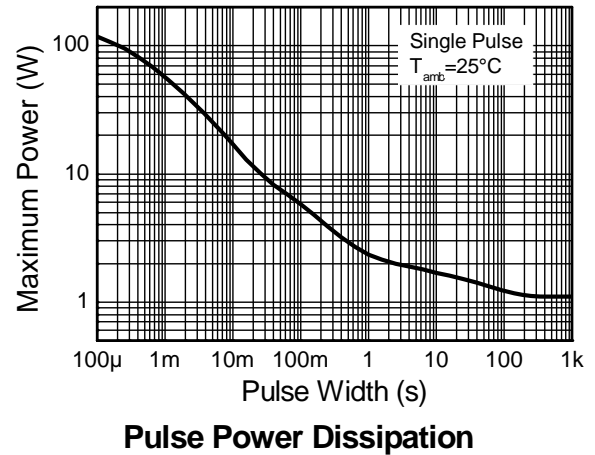
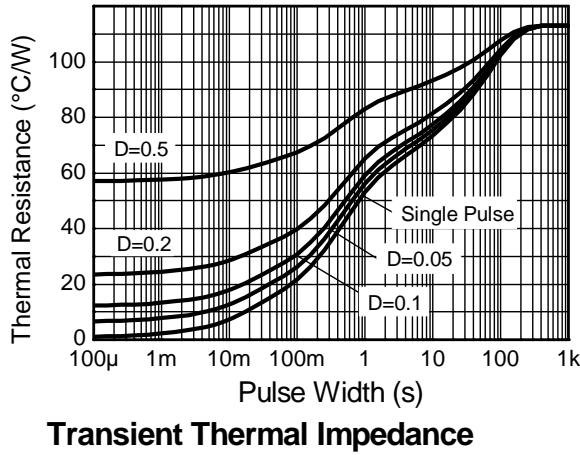
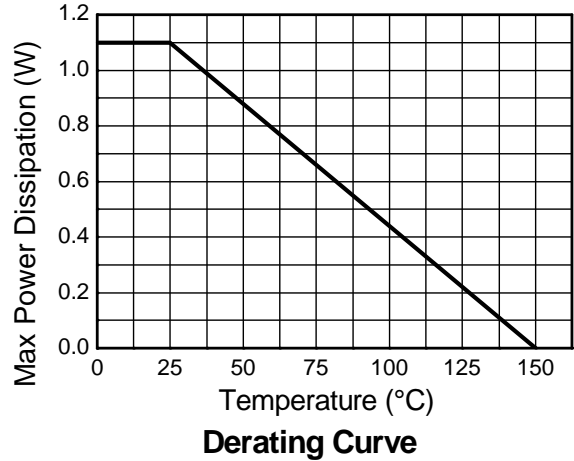
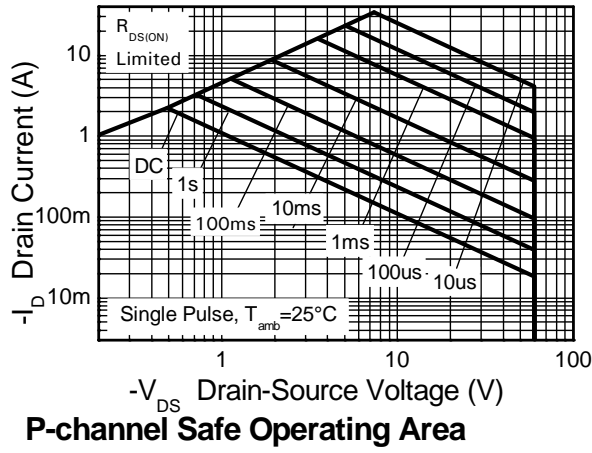
Characteristic			Symbol	Value	Unit	
Drain-Source voltage			V_{DSS}	-60	V	
Gate-Source voltage			V_{GS}	± 20	V	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 5)	I_D	-3.0	A	
		$T_A = 70^\circ\text{C}$ (Note 5)		-2.4		
		(Note 4)		-2.3		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 6)	I_{DM}	-13.6	A	
Continuous Source current (Body diode)			(Note 5)	I_S	-2.5	A
Pulsed Source current (Body diode)			(Note 6)	I_{SM}	-13.6	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Power dissipation	Linear derating factor	(Note 4)	P_D	1.1	W
				8.8	
		(Note 5)		1.92	
				15.4	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	113	$^\circ\text{C}/\text{W}$	
	(Note 5)		65		
Operating and storage temperature range			T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

- Notes:
4. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 5. Same as note (4), except the device is measured at $t \leq 5$ sec.
 6. Same as note (4), except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.

Thermal Characteristics

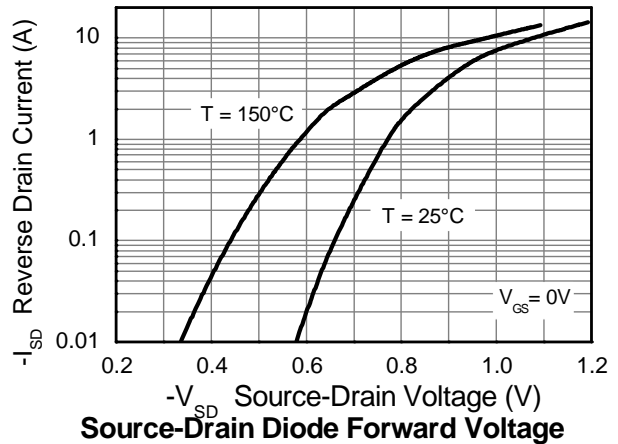
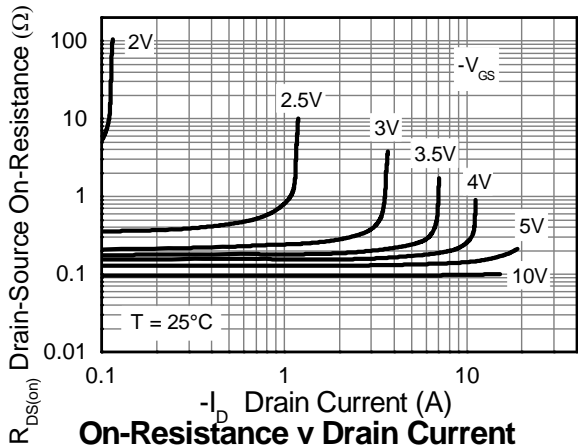
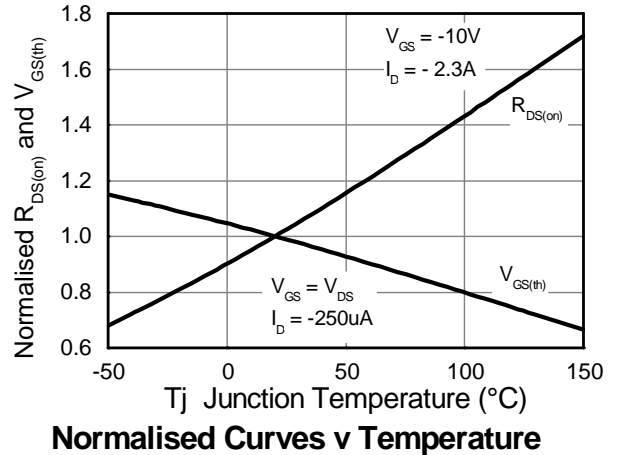
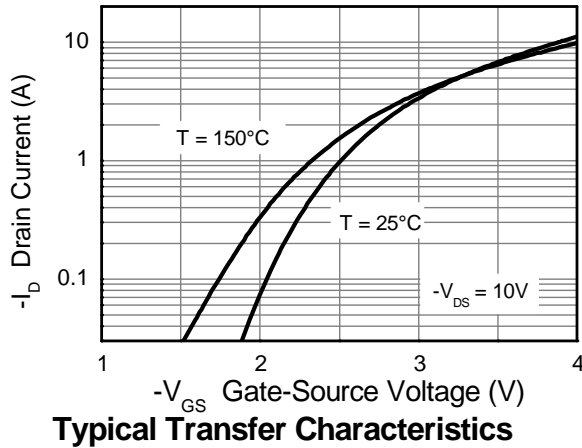
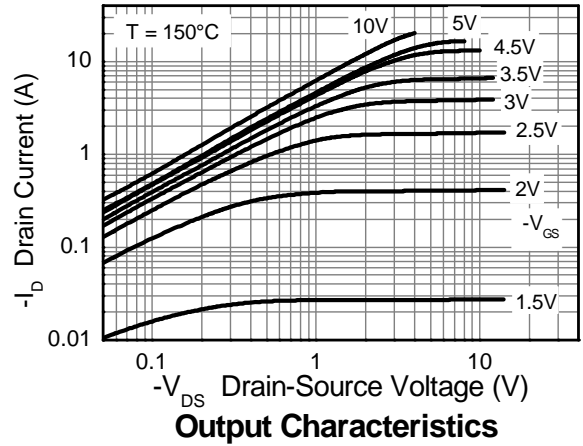
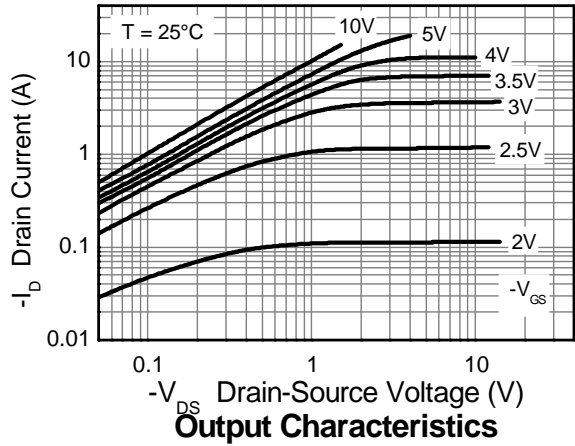


Electrical Characteristics @T_A = 25°C unless otherwise specified

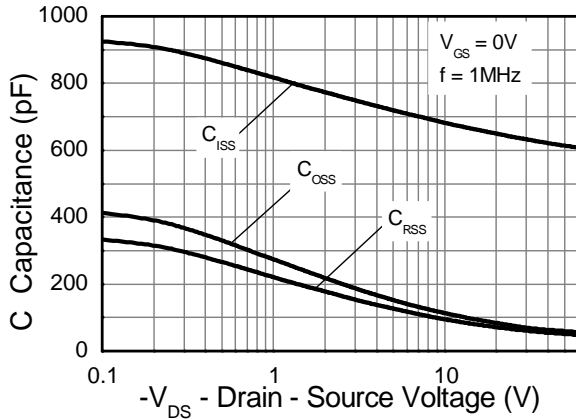
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	-3.0	V	I _D = -250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 7)	R _{DS(on)}	—	0.100	0.125	Ω	V _{GS} = -10V, I _D = -2.3A
			0.130	0.190		V _{GS} = -4.5V, I _D = -1.9A
Forward Transconductance (Notes 7 & 8)	g _{fs}	—	4.7	—	S	V _{DS} = -15V, I _D = -2.3A
Diode Forward Voltage (Note 7)	V _{SD}	—	-0.85	-0.95	V	I _S = -2A, V _{GS} = 0V
Reverse recovery time (Note 8)	t _{rr}	—	25.1	—	ns	I _F = -1.7A, di/dt = 100A/μs
Reverse recovery charge (Note 8)	Q _{rr}	—	27.2	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	—	637	—	pF	V _{DS} = -30V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oSS}	—	70	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	53	—	pF	
Total Gate Charge (Note 9)	Q _g	—	9.8	—	nC	V _{GS} = -5.0V
Total Gate Charge (Note 9)	Q _g	—	17.7	—	nC	V _{GS} = -10V V _{DS} = -30V I _D = -2.3A
Gate-Source Charge (Note 9)	Q _{gs}	—	1.6	—	nC	
Gate-Drain Charge (Note 9)	Q _{gd}	—	4.4	—	nC	
Turn-On Delay Time (Note 9)	t _{D(on)}	—	2.6	—	ns	V _{DD} = -30V, V _{GS} = -10V I _D = -1A, R _G ≅ 6.0Ω
Turn-On Rise Time (Note 9)	t _r	—	3.4	—	ns	
Turn-Off Delay Time (Note 9)	t _{D(off)}	—	26.2	—	ns	
Turn-Off Fall Time (Note 9)	t _f	—	11.3	—	ns	

- Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 8. For design aid only, not subject to production testing.
 9. Switching characteristics are independent of operating junction temperatures.

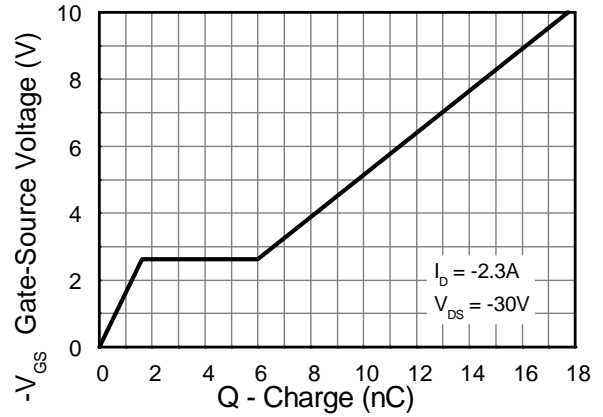
Typical Characteristics



Typical Characteristics - continued

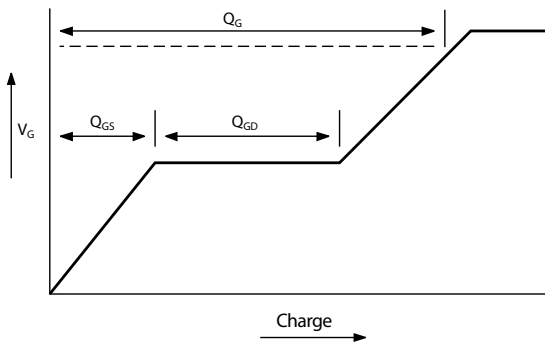


Capacitance v Drain-Source Voltage

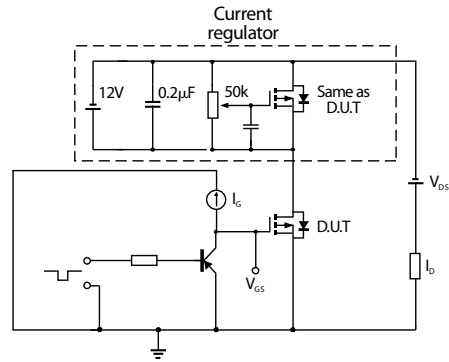


Gate-Source Voltage v Gate Charge

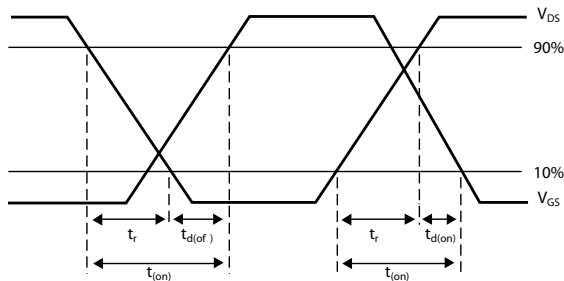
Test Circuits



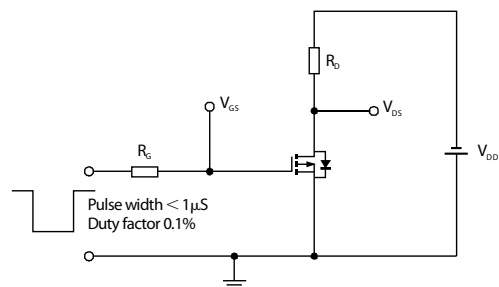
Basic gate charge waveform



Gate charge test circuit

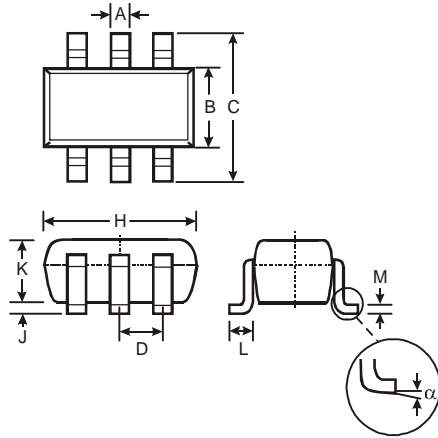


Switching time waveforms



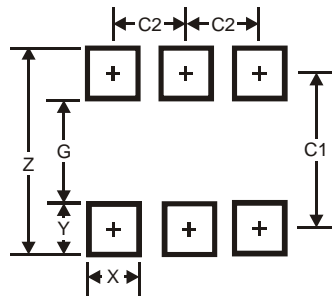
Switching time test circuit

Package Outline Dimensions



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

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